WSD6042DN33

Dual N-Channel MOSFET

General Description

The WSD6042DN33 is the highest performance trench Dual N-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSD6042DN33 meet the RoHS and Green Product requirement 100% E_{AS} guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E_{AS} Guaranteed
- Green Device Available

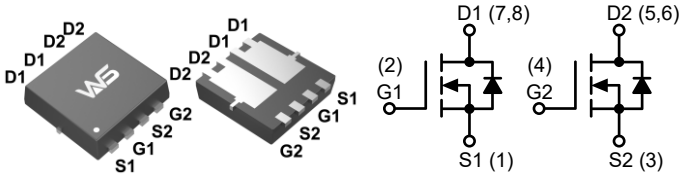
Product Summery

BV_{DSS}	$R_{DS(ON)}$	I_D
60V	14mΩ	45A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3X3-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V [1]	45	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V [1]	22	
I_{DM}	Pulsed Drain Current [2]	150	
E_{AS}	Single Pulse Avalanche Energy [3]	50	mJ
I_{AS}	Avalanche Current	14	A
P_D@T_C=25°C	Power Dissipation [4]	36	W
P_D@T_A=25°C	Power Dissipation [4]	2.5	
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	

Thermal Data

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient [1]	---	80	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case [1]	---	3.6	

Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250μA	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C, I_D=1mA	---	0.063	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance [2]	V_{GS}=10V , I_D=15A	---	14	15	mΩ
		V_{GS}=4.5V , I_D=10A	---	17	19	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=250μA	1.0	1.7	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.08	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25°C	---	---	1.0	μA
		V_{DS}=48V , V_{GS}=0V , T_J=55°C	---	---	5.0	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
g_{fs}	Forward Transconductance	V_{DS}=5V , I_D=15A	---	35	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f = 1.0MHz	---	3.2	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=30V , V_{GS}=4.5V , I_D=12A	---	12.6	---	nC
Q_{gs}	Gate-Source Charge		---	2.2	---	
Q_{gd}	Gate-Drain Charge		---	1.3	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GEN}=10V , R_G=3.3Ω , I_D=10A	---	3.5	---	ns
T_r	Rise Time		---	11	---	
$T_{d(off)}$	Turn-Off Delay Time		---	10	---	
T_f	Fall Time		---	5.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f = 1.0MHz	---	710	---	pF
C_{oss}	Output Capacitance		---	220	---	
C_{rss}	Reverse Transfer Capacitance		---	14	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy [5]	V_{DD}=25V , L=0.5mH , I_{AS}=22A	50	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current [1,6]	V_G=V_D=0V , Force Current	---	---	45	A
I_{SM}	Pulsed Source Curren [2,6]		---	---	90	A
V_{SD}	Diode Forward Voltage [2]	V_{GS}=0V , I_S=1A , T_J=25°C	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=15A, dI/dt=100A/μs,T_J=25°C	---	22	---	ns
Q_{rr}	Reverse Recovery Charge		---	51	---	nC

Note:

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t≤10sec.
2. The data tested by pulsed , pulse width ≤ 300μs , duty cycle ≤ 2%
3. The E_{AS} data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.5mH, I_{AS}=22A
4. The power dissipation is limited by 150°C junction temperature.
5. The Min. value is 100% E_{AS} tested guarantee.
6. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

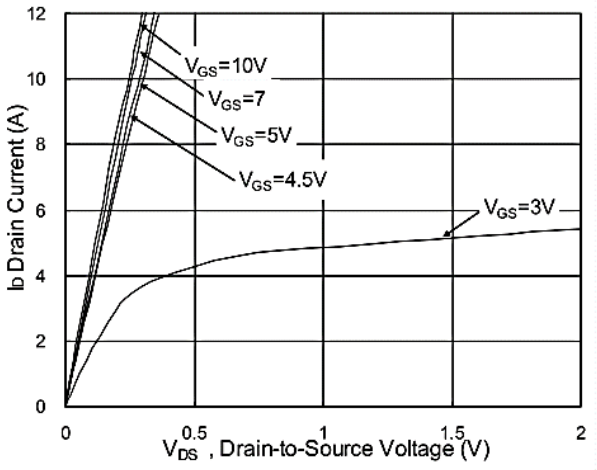


Fig.1 Typical Output Characteristics

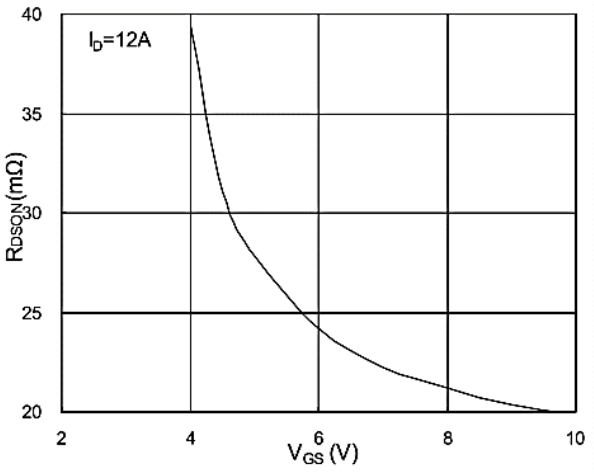


Fig.2 On-Resistance v.s Gate-Source

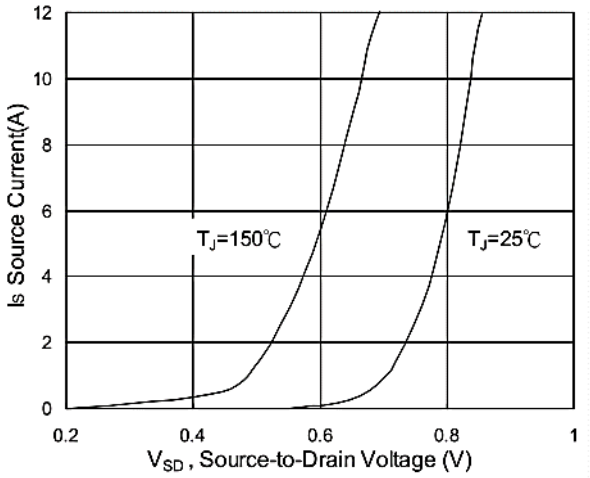


Fig.3 Forward Characteristics of Reverse

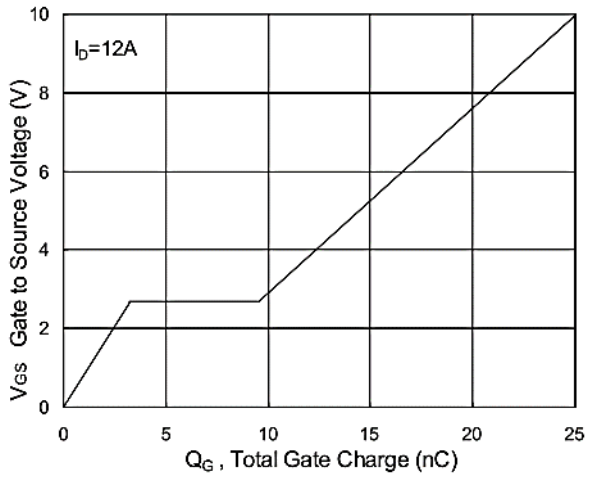


Fig.4 Gate-Charge Characteristics

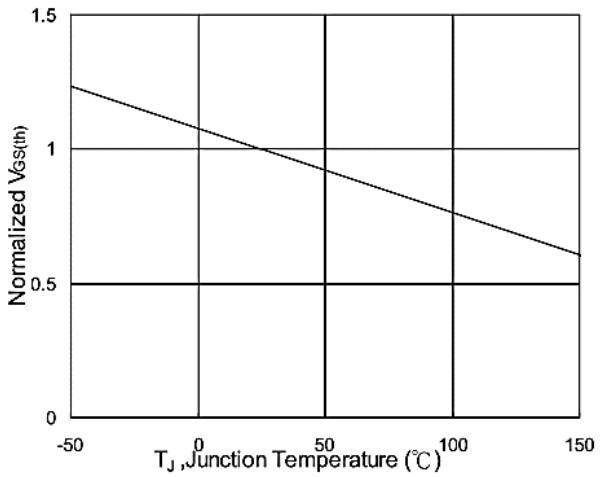


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

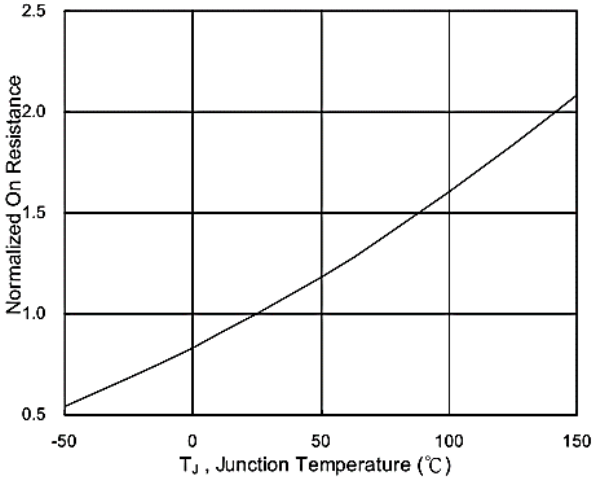


Fig.6 Normalized R_{DSON} v.s T_J

Typical Characteristics (Cont.)

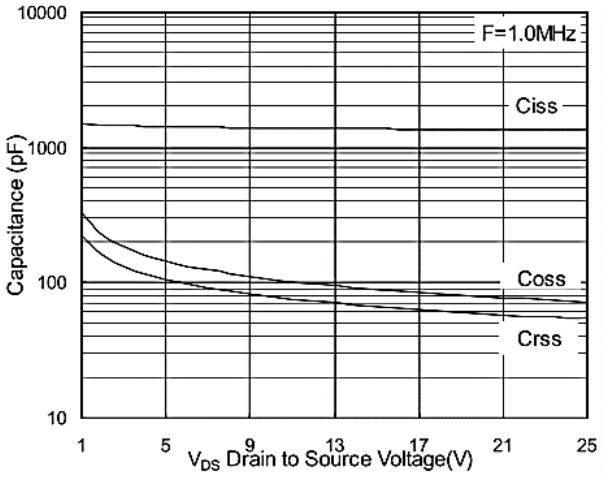


Fig.7 Capacitance

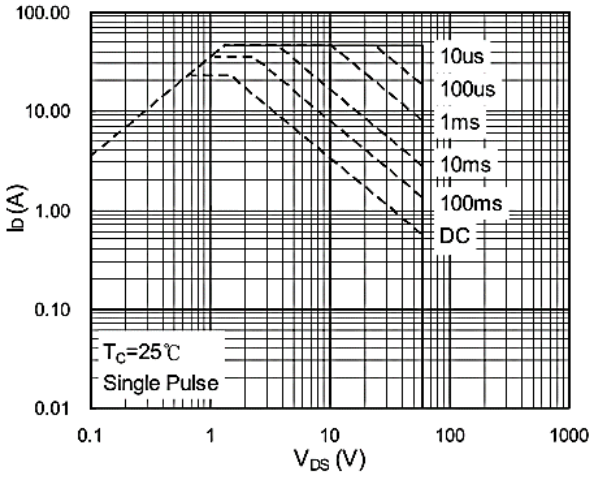


Fig.8 Safe Operating Area

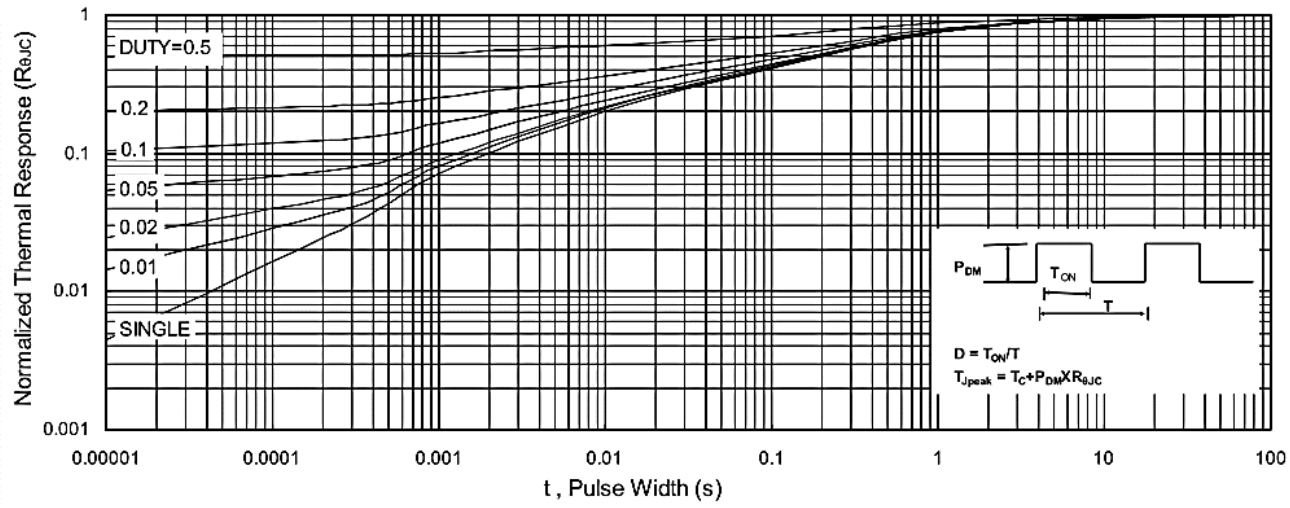


Fig.9 Normalized Maximum Transient Thermal Impedance

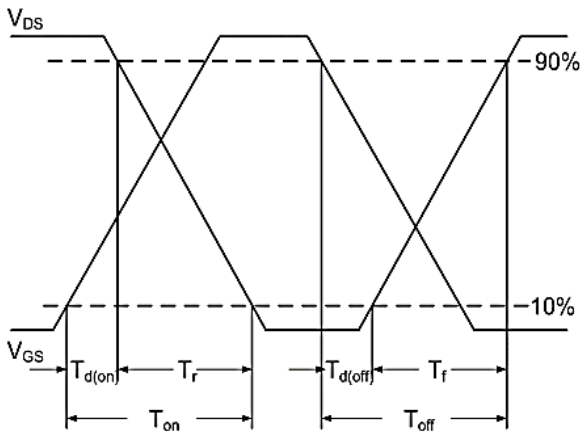


Fig.10 Switching Time Waveform

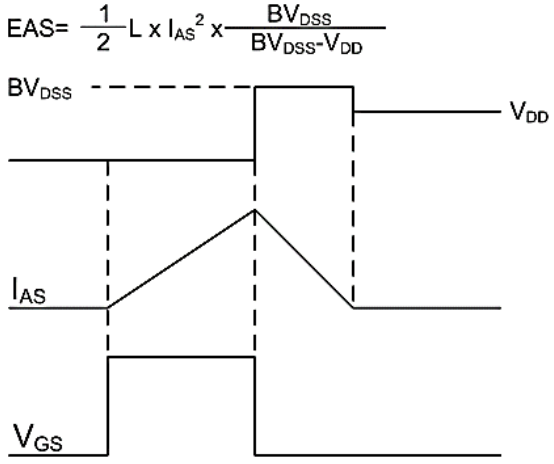
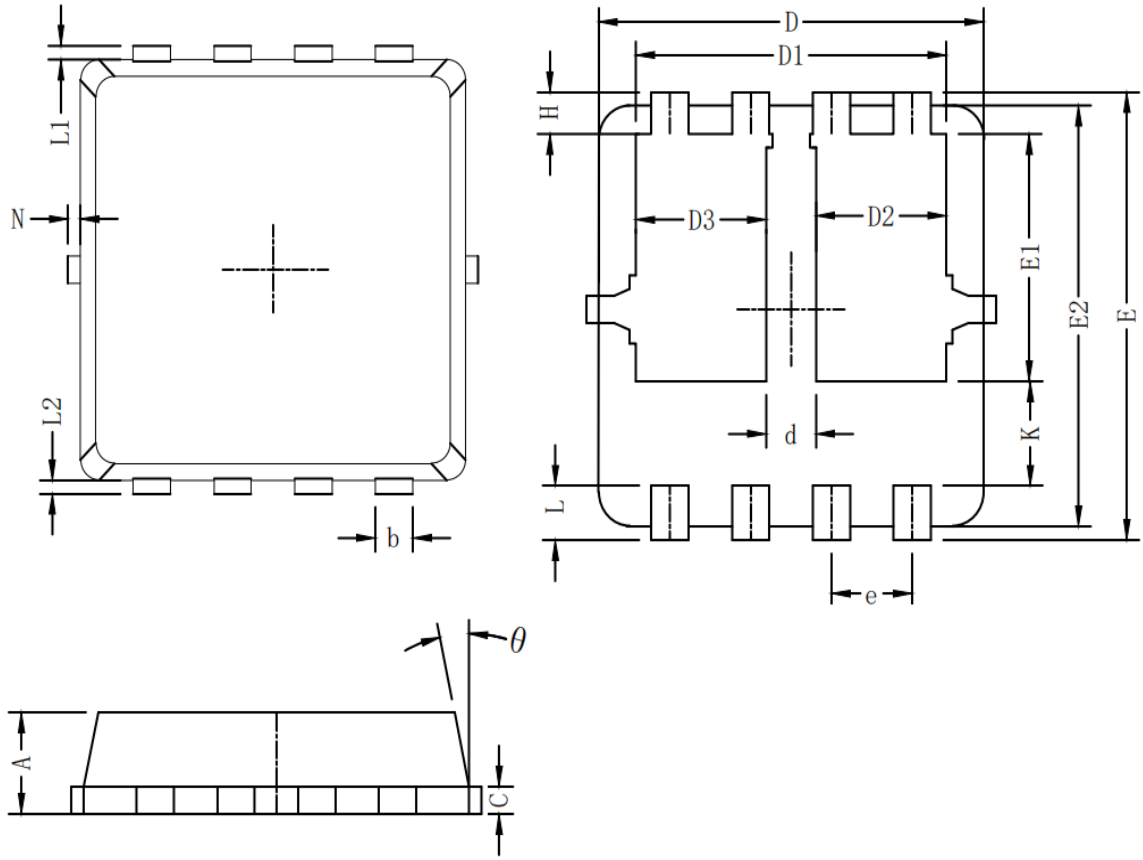


Fig.11 Unclamped Inductive Waveform

Packaging information



Symbol	Dim in mm		
	min	typ	max
A	0.6	0.75	0.9
b	0.2	0.3	0.4
C	0.15	0.2	0.25
D	3	3.1	3.2
D1	2.3	2.45	2.6
D2/D3	0.8	1	1.2
E	3.15	3.3	3.45
E1	1.43	1.73	1.93
E2	2.9	3.05	3.2
e	0.65BSC		
H	0.2	0.35	0.5
K	0.57	0.77	0.87
L	0.3	0.4	0.5
L1/L2	0.1REF		
θ	8°	10°	13°
N	0		0.15
d	0.3	0.4	0.5

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